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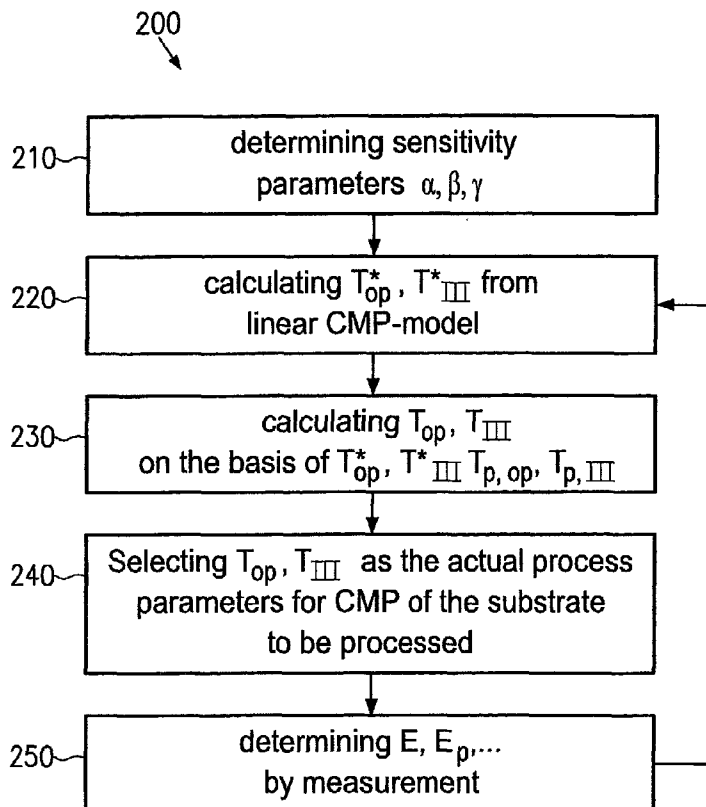
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(54) Title: METHOD AND SYSTEM FOR CONTROLLING THE CHEMICAL MECHANICAL POLISHING OF SUBSTRATES BY CALCULATING AN OVERPOLISHING TIME AND/OR A POLISHING TIME OF A FINAL POLISHING STEP



(57) Abstract: A method and a controller 150 for the chemical mechanical polishing (CMP) of substrates 121 and, in particular, for the chemical mechanical polishing of metallization layers is disclosed. In a linear model of the CMP process, the erosion of the metallization layer to be treated is determined by the overpolish time and possibly by an extra polish time on a separate polishing platen for polishing the dielectric layer, wherein the CMP inherent characteristics are represented by sensitivity parameters derived empirically. Moreover, the control operation is designed so that even with a certain inaccuracy of the sensitivity parameters due to subtle process variations, a reasonable controller response is obtained.



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